

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3858	361/111	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 12:42
L2	885	1 and (esd electrostatic) and (resistor resistance (first near "RC")) and (capacitor capacitance (second near "RC"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 12:42
L3	5014	361/56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 12:43
L4	1347	L3 and (esd electrostatic) and (resistor resistance (first near "RC")) and (capacitor capacitance (second near "RC"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 12:43
L5	162	2 not L4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 12:43
L6	1228	361/91.1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:04
L7	276	6 and (esd electrostatic) and (resistor resistance (first near "RC")) and (capacitor capacitance (second near "RC"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:05
L8	71	7 not 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:05
L9	2173	361/118	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:06

L10	269	9 and (esd electrostatic) and (resistor resistance (first near "RC")) and (capacitor capacitance (second near "RC"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:06
L11	79	10 not 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:06
L12	70	11 not 4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:06
L20	45	(esd electrostatic) and (first near "RC") and (second near "RC")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 13:46
S1	2	"US 20080285199"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/03/03 13:17
S2	0	("(6,177,2986,618,2335,982,601).pn.").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/03/03 13:28
S3	0	("6,177,2986,618,2335,982,601").pn.	US-PGPUB; USPAT	OR	ON	2009/03/03 13:28
S4	3	((("6177298") or ("6618233") or ("5982601"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/03/03 13:28
S5	15	("5452171" "5561577" "5576557" "5728612" "5754381" "5894153" "5895940" "5905288" "5909347" "6011681" "6091595" "6130117" "6288884" "6433979").PN. OR ("6618233").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:29
S6	16	("5272097" "5290724" "5400202" "5453384" "5528188" "5610425" "5708288").PN. OR ("6177298").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:30
S7	29	("4400711" "4484244" "4595941" "4633283" "5010380" "5072273" "5157573" "5182220" "5276350" "5287241" "5400202" "5416494" "5418383" "5442220" "5452171" "5465189").PN. OR ("5610425").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:31
S8	34	("5077591").PN. OR ("5452171").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:32
S9	9	("5528188" "5541801" "5734541" "5852541").PN. OR ("5982601").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:38
S10	579	(esd electrostatic overvoltage) and ("SCR" (silicon near rectifier)) and (inverter\$1) and (resistor\$1) and (capacitor\$1)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:40

S11	13	("20020053704" "20020153571" "20030076636" "20060055438" "5255146" "5565790" "5946177" "6008970" "6400540" "6765771" "6768616" "7102864" "7212387").PN. OR ("7440248").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/03 13:45
S12	64365	(inverter\$1) with (bipolar MOSFET\$1 FET\$1 transistor\$1)	US-PGPUB; USPAT	OR	ON	2009/03/03 16:17
S13	639	S12 same (esd electrostatic)	US-PGPUB; USPAT	OR	ON	2009/03/03 16:17
S14	38	(inverter\$1) with (control\$3) with (gate\$1) with (transistor\$1) with ("SCR" (silicon near rectifier))	US-PGPUB; USPAT	OR	ON	2009/03/04 09:46
S15	230103	(esd electrostatic)	US-PGPUB; USPAT	OR	ON	2009/03/04 09:46
S16	2684	S15 and ("SCR" (silicon near rectifier))	US-PGPUB; USPAT	OR	ON	2009/03/04 09:47
S17	490	S16 and (inverter\$1)	US-PGPUB; USPAT	OR	ON	2009/03/04 09:47
S18	430	S17 and (trigger\$3 "RC" (resistor with capacitor))	US-PGPUB; USPAT	OR	ON	2009/03/04 09:47
S19	3097	(benefit advantage\$4) with (bipolar with transistor\$1)	US-PGPUB; USPAT	OR	ON	2009/03/04 11:19
S20	31	(benefit advantage\$4) with (bipolar with transistor\$1) with (esd electrostatic)	US-PGPUB; USPAT	OR	ON	2009/03/04 11:19
S21	2	("5982601").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/19 10:38
S22	2	"US 20080285199"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/11/19 10:41
S23	5014	361/56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 11:10
S24	1347	S23 and (esd electrostatic) and (resistor resistance (first near "RC")) and (capacitor capacitance (second near "RC"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/19 11:11
S25	14	("5440162" "5654862" "5946177" "6046087" "6172383" "6429489" "6618230" "6704179" "6867461" "6898061" "6917207" "6919602" "7027275" "7102862").PN. OR ("7545614").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/19 11:28
S26	66	("5239440" "5287241" "5440162" "5559659" "5654862" "5745323").PN. OR ("5946177").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/11/19 11:29

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L21	0	((esd electrostatic) and (first near "RC") and (second near "RC") and (transistor PMOS NMOS MOSFET FET) and (thyristor "SCR" (silicon near rectifier))).clm.	US-PGPUB; UPAD	OR	ON	2009/11/19 14:16
L22	8	((esd electrostatic) and (first near "RC") and (second near "RC") and (transistor PMOS NMOS MOSFET FET)).clm.	US-PGPUB; UPAD	OR	ON	2009/11/19 14:17

11/19/2009 2:24:18 PM

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